7(Amended). The method as described in claim 6, further comprising the step of selective KOH etching to remove [RIE-induced] reactive ion etching induced surface damage.

9(Amended). The method as described in claim 1, wherein the grating comprises [a] rectangular [grating] projections.

10(Amended). The method as described in claim 1, wherein the grating comprises [a] triangular [grating] projections.

12(Amended). The method as described in claim [1] 2, wherein the grating is chosen to have optimal performance within the solar [cell] spectrum.

13(Amended). The method as described in claim 1, further comprising the step of anti-reflection coating the [grating] surface of the grating upon which light is incident.

15(Amended). A method for producing a solar cell having increased absorption of light radiation incident on a surface thereof which comprises the steps of: (a) forming a grating on the surface of said solar cell upon which the light is incident; (b) removing surface contamination; (c) forming an n-type junction using gas source doping; and (d) forming n- and p-electrical contacts.

17(Amended). The method as described in claim 16, further comprising the step of removing reactive ion etching-induced surface damage using [wet-chemical] wet chemical etching.

18(Amended). The method as described in claim 17, wherein said step of [wet-chemical] wet chemical etching comprises exposing the surface to KOH and nitric acid solutions.

20(Amended). A method for producing a solar cell having increased absorption of light radiation incident on a surface thereof which comprises the steps of: (a) forming a grating on the surface of said solar cell upon which the light is incident; (b) cleaning the surface to remove surface contamination; (c) forming an n-type junction by ion implantation; (d) annealing the solar cell formed thereby; and (e) forming n- and p-electrical contacts.